

NPN POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/509

Devices

2N6338

2N6341

Qualified Level

JANTX
JANTXV

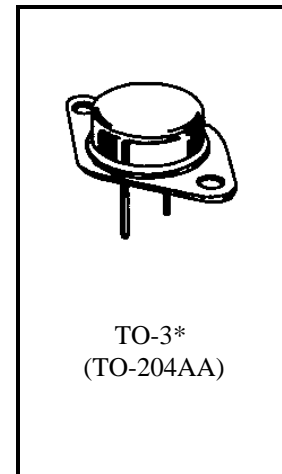
MAXIMUM RATINGS

Ratings	Symbol	2N6338	2N6341	Unit
Collector-Emitter Voltage	V_{CEO}	100	150	Vdc
Collector-Base Voltage	V_{CBO}	120	180	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Base Current	I_B	10		Adc
Collector Current	I_C	25		Adc
Total Power Dissipation ⁽¹⁾	P_T	@ $T_A = +25^{\circ}C$	200	W
		@ $T_C = +100^{\circ}C$	112	W
Operating & Storage Junction Temperature Range	T_{op}, T_{stg}	-65 to +175		$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.875	$^{\circ}C/W$

1) Derate linearly 1.14 W/ $^{\circ}C$ for $T_C = +25^{\circ}C$ and $T_C = +200^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 50$ mAdc	2N6338 2N6341	$V_{(BR)CEO}$	100 150	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 50$ Vdc $V_{CE} = 75$ Vdc	2N6338 2N6341	I_{CEO}	50	μ Adc
Collector-Emitter Cutoff Current $V_{CE} = 100$ Vdc, $V_{BE} = 1.5$ Vdc $V_{CE} = 150$ Vdc, $V_{BE} = 1.5$ Vdc	2N6338 2N6341	I_{CEX}	10 10	μ Adc
Emitter-Base Cutoff Current $V_{EB} = 6.0$ Vdc		I_{EBO}	100	μ Adc
Collector-Base Cutoff Current $V_{CB} = 120$ Vdc $V_{CB} = 180$ Vdc	2N6338 2N6341	I_{CEO}	10 10	μ Adc

2N6338, 2N6341 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
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ON CHARACTERISTICS ⁽²⁾

Forward-Current Transfer Ratio I _C = 0.5 Adc, V _{CE} = 2.0 Vdc I _C = 10 Adc, V _{CE} = 2.0 Vdc I _C = 25 Adc, V _{CE} = 2.0 Vdc	h _{FE}	40 30 12	120	
Collector-Emitter Saturation Voltage I _C = 10 Adc, I _B = 1.0 Adc I _C = 25 Adc, I _B = 2.5 Adc	V _{CE(sat)}		1.0 1.8	Vdc
Base-Emitter Saturation Voltage I _C = 10 Adc, I _B = 1.0 Adc	V _{BE(sat)}		1.8	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 10 MHz	h _{fe}	4.0	12	
Output Capacitance V _{CB} = 10 Vdc, I _E = 0, 0.1 MHz ≤ f ≤ 1.0 MHz	C _{obo}		450	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 80 Vdc; I _C = 10 Adc; I _B = 1.0 Adc	t _{on}		0.5	μs
Turn-Off Time V _{CC} = 80 Vdc; I _C = 10 Adc; I _{B1} = I _{B2} = 1.0 Adc	t _{off}		1.25	μs
Storage Time V _{CC} = 80 Vdc; I _C = 10 Adc; I _{B1} = I _{B2} = 1.0 Adc	t _s		1.0	μs

SAFE OPERATING AREA

DC Tests T _C = +25°C, 1 Cycle, t = 1.0 s				
Test 1 V _{CE} = 8.0 Vdc, I _C = 25 Adc				
	All Types			
Test 2 V _{CE} = 14 Vdc, I _C = 14 Adc				
	All Types			
Test 3 V _{CE} = 100 Vdc, I _C = 100 mAdc				
	2N6338			
V _{CE} = 150 Vdc, I _C = 66 mAdc				
	2N6341			

(2) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.

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